

2SK3077

900 MHz BAND AMPLIFIER APPLICATIONS (GSM)

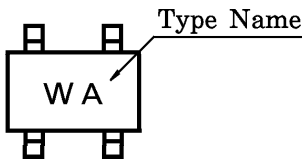
- Output Power : $P_O = 15.0 \text{ dBmW (Min.)}$
- Gain : $G_P = 15.0 \text{ dB (Min.)}$
- Drain Efficiency : $\eta_D = 20\% \text{ (Typ.)}$

MAXIMUM RATINGS (Ta = 25°C)

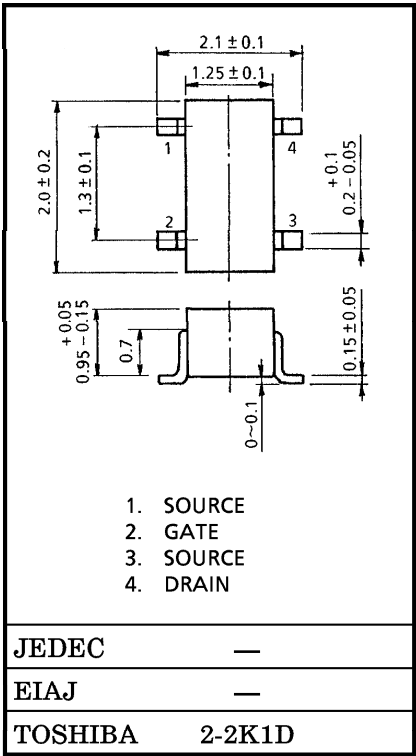
CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	10	V
Gate-Source Voltage	V_{GSS}	5	V
Drain Current	I_D	0.1	A
Power Dissipation	P_D^*	0.1	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-45~150	°C

* : $T_c = 25^\circ\text{C}$ When mounted on a 1.6 mm glass epoxy PCB

MARKING



Unit in mm



961001EAA1

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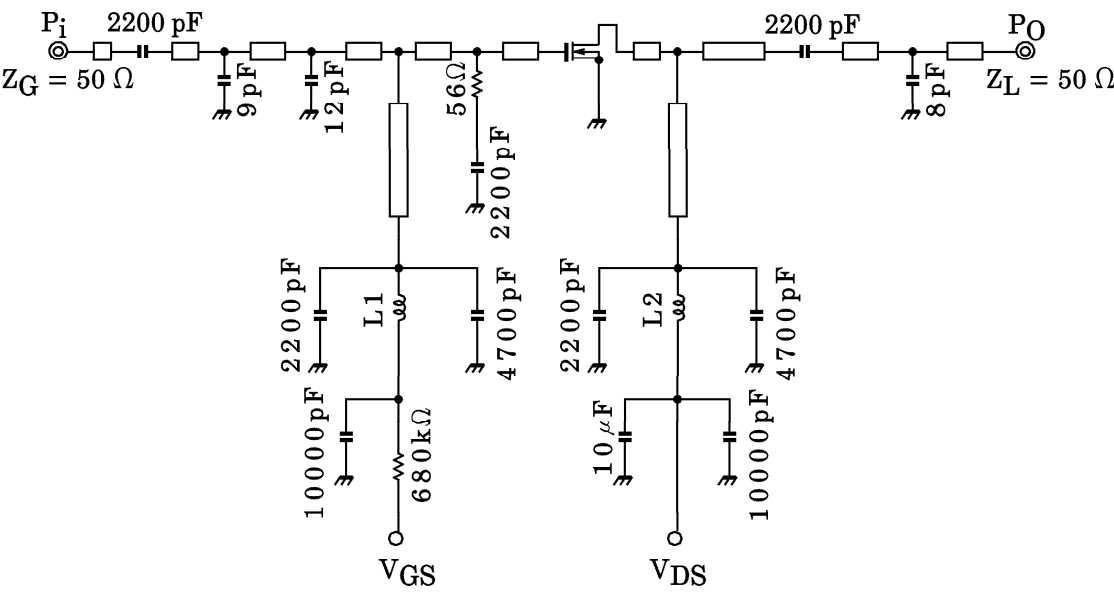
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Power	PO	VDS = 4.8 V	15.0	—	—	dBmW
Drain Efficiency	η_D	Iidle = 43 mA (VGS = adjust) f = 915 MHz, Pi = 0 dBmW	—	20.0	—	%
Power Gain	GP	ZG = ZL = 50 Ω	15.0	—	—	dB
Threshold Voltage	Vth	VDS = 4.8 V, ID = 0.5 mA	0.25	—	1.25	V
Drain Cut-off Current	IDSS	VDS = 10 V, VGS = 0 V	—	—	10	μ A
Gate-Source Leakage Current	IGSS	VGS = 5 V, VDS = 0 V	—	—	5	μ A

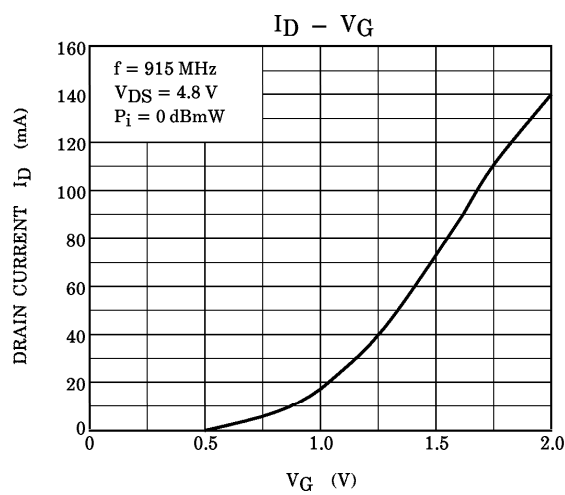
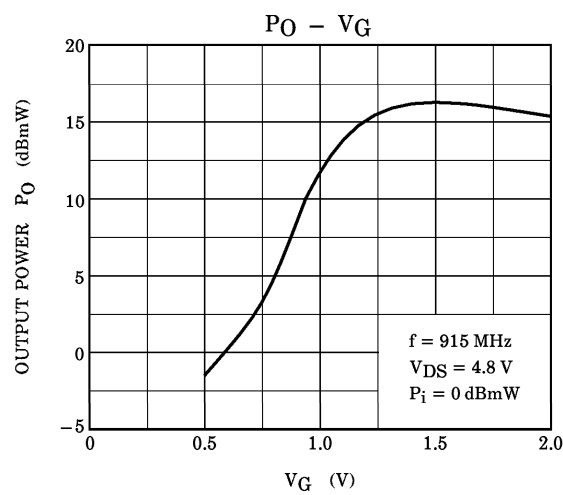
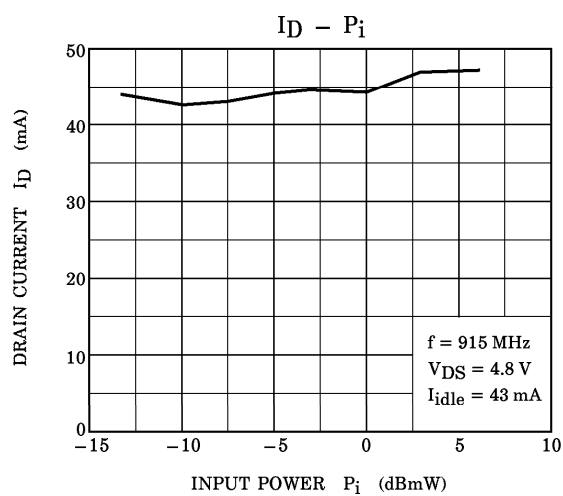
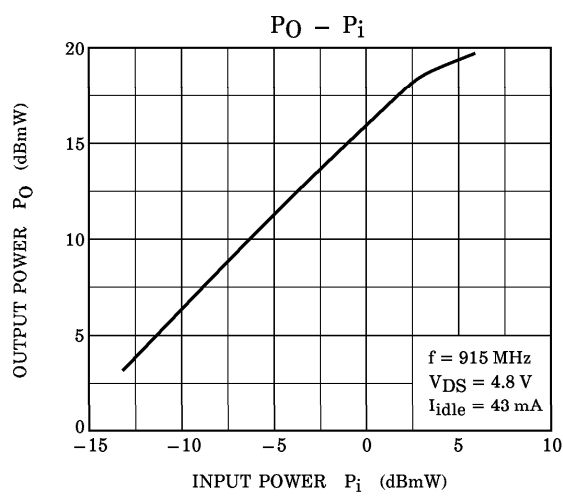
CAUTION

This transistor is the electrostatic sensitive device.
Please handle with caution.

RF OUTPUT POWER TEST FIXTURE



L1 : ϕ 0.6 mm, 5.5 mmID, 5T
L2 : ϕ 0.6 mm, 5.5 mmID, 8T



CAUTION
These are only typical curves and devices are not necessarily guaranteed at these curves.